

### CLAIMS

1. (currently amended) A method for treating powder particles of a  $\text{Cu(In,Ga)Se}_2$  compound, comprising the steps of:  
placing the powder particles and sulfur into a vessel; ~~and~~  
heating the vessel contents comprising the powder particles and the sulfur; and  
maintaining the vessel contents at a constant temperature for a period of time  
sufficient to heat the particles.
2. (currently amended) The method according to claim 1, comprising filling the particles and the sulfur into a two-zone ampoule, placing the powder particles into one of the zones and placing the ~~amount of~~ sulfur into the other zone.
3. (currently amended) The method according to claim 1, comprising heating the powder particles to a temperature between 400 °C and 600 °C (752 °F and 1112 °F).
4. (previously presented) The method according to claim 1, comprising heating the sulfur to a temperature of about 100 °C (212 °F).
5. (previously presented) The method according to claim 1, comprising maintaining the particles and the sulfur at a constant temperature for a period of time between one hour and 50 hours.
6. (previously presented) The method according to claim 1, comprising filling a mixture of the powder particles and the sulfur into an ampoule.

7. (currently amended) The method according to ~~claim 7~~ claim 6, comprising heating the mixture to a temperature between 300 °C and 600 °C (572 °F and 1112 °F).
8. (currently amended) The method according to ~~claim 7~~ claim 6, comprising maintaining the mixture at a given temperature for a period of time between five minutes and four hours.
9. (currently amended) A mono-particle membrane solar cell comprising a back contact, a mono-particle membrane, at least one semiconductor layer and a front contact, wherein the mono-particle membrane contains the powder particles treated according to the method of claim 1 .
10. (new) The method according to claim 1, wherein the vessel contents consist of the powder particles and the sulfur.
11. (new) Treated powder particles of a  $\text{Cu(In,Ga)Se}_2$  compound, produced according to the method of claim 1.